

SEMiX302GB126HDs



SEMiX® 2s

Trench IGBT Modules

SEMiX302GB126HDs

Features

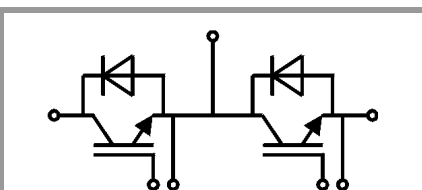
- Homogeneous Si
- Trench = Trenchgate technology
- $V_{CE(sat)}$ with positive temperature coefficient
- High short circuit capability
- UL recognised file no. E63532

Typical Applications*

- AC inverter drives
- UPS
- Electronic Welding

Remarks

- Case temperatur limited to $T_C=125^\circ\text{C}$ max.
- Not for new design



GB

Absolute Maximum Ratings				
Symbol	Conditions	Values	Unit	
IGBT				
V_{CES}	$T_j = 25^\circ\text{C}$	1200	V	
I_C	$T_j = 150^\circ\text{C}$	$T_c = 25^\circ\text{C}$	311	A
		$T_c = 80^\circ\text{C}$	218	A
I_{Cnom}		200	A	
I_{CRM}	$I_{CRM} = 2 \times I_{Cnom}$	400	A	
V_{GES}		-20 ... 20	V	
t_{psc}	$V_{CC} = 600\text{ V}$ $V_{GE} \leq 20\text{ V}$ $V_{CES} \leq 1200\text{ V}$	$T_j = 125^\circ\text{C}$	10	μs
	T_j			
Inverse diode				
I_F	$T_j = 150^\circ\text{C}$	$T_c = 25^\circ\text{C}$	292	A
		$T_c = 80^\circ\text{C}$	202	A
I_{Fnom}		200	A	
I_{FRM}	$I_{FRM} = 2 \times I_{Fnom}$	400	A	
I_{FSM}	$t_p = 10\text{ ms, sin } 180^\circ, T_j = 25^\circ\text{C}$	1300	A	
T_j		-40 ... 150	$^\circ\text{C}$	
Module				
$I_{t(RMS)}$	$T_{terminal} = 80^\circ\text{C}$	600	A	
T_{stg}		-40 ... 125	$^\circ\text{C}$	
V_{isol}	AC sinus 50Hz, $t = 1\text{ min}$	4000	V	

Characteristics					
Symbol	Conditions	min.	typ.	max.	Unit
IGBT					
$V_{CE(sat)}$	$I_C = 200\text{ A}$ $V_{GE} = 15\text{ V}$ chipelevel	$T_j = 25^\circ\text{C}$	1.7	2.10	V
		$T_j = 125^\circ\text{C}$	2.0	2.45	V
V_{CE0}	chipelevel	$T_j = 25^\circ\text{C}$	1	1.2	V
		$T_j = 125^\circ\text{C}$	0.9	1.1	V
r_{CE}	$V_{GE} = 15\text{ V}$ chipelevel	$T_j = 25^\circ\text{C}$	3.5	4.5	$\text{m}\Omega$
		$T_j = 125^\circ\text{C}$	5.5	6.8	$\text{m}\Omega$
$V_{GE(th)}$	$V_{GE}=V_{CE}, I_C = 8\text{ mA}$	5	5.8	6.5	V
I_{CES}	$V_{GE} = 0\text{ V}$ $V_{CE} = 1200\text{ V}$	$T_j = 25^\circ\text{C}$		2.7	mA
		$T_j = 125^\circ\text{C}$			mA
C_{ies}	$V_{CE} = 25\text{ V}$ $V_{GE} = 0\text{ V}$	$f = 1\text{ MHz}$	14.4		nF
C_{oes}		$f = 1\text{ MHz}$	0.75		nF
C_{res}		$f = 1\text{ MHz}$	0.65		nF
Q_G	$V_{GE} = -8\text{ V...} + 15\text{ V}$		1600		nC
R_{Gint}	$T_j = 25^\circ\text{C}$		3.75		Ω
$t_{d(on)}$	$V_{CC} = 600\text{ V}$ $I_C = 200\text{ A}$	$T_j = 125^\circ\text{C}$	320		ns
t_r	$V_{GE} = \pm 15\text{ V}$	$T_j = 125^\circ\text{C}$	50		ns
E_{on}	$R_{Gon} = 2.8\ \Omega$	$T_j = 125^\circ\text{C}$	30		mJ
$t_{d(off)}$	$R_{Goff} = 2.8\ \Omega$	$T_j = 125^\circ\text{C}$	600		ns
t_f		$T_j = 125^\circ\text{C}$	100		ns
E_{off}		$T_j = 125^\circ\text{C}$	26		mJ
$R_{th(j-c)}$	per IGBT			0.12	K/W

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Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
Inverse diode						
$V_F = V_{EC}$	$I_F = 200\text{ A}$ $V_{GE} = 0\text{ V}$ chipllevel	$T_j = 25\text{ }^\circ\text{C}$		1.6	1.80	V
		$T_j = 125\text{ }^\circ\text{C}$		1.6	1.8	V
V_{F0}	chipllevel	$T_j = 25\text{ }^\circ\text{C}$	0.9	1	1.1	V
		$T_j = 125\text{ }^\circ\text{C}$	0.7	0.8	0.9	V
r_F	chipllevel	$T_j = 25\text{ }^\circ\text{C}$	2.5	3.0	3.5	m Ω
		$T_j = 125\text{ }^\circ\text{C}$	3.5	4.0	4.5	m Ω
I_{RRM}	$I_F = 200\text{ A}$	$T_j = 125\text{ }^\circ\text{C}$		290		A
Q_{rr}	$di/dt_{off} = 5900\text{ A}/\mu\text{s}$	$T_j = 125\text{ }^\circ\text{C}$		55		μC
E_{rr}	$V_{GE} = -15\text{ V}$ $V_{CC} = 600\text{ V}$	$T_j = 125\text{ }^\circ\text{C}$		22.5		mJ
$R_{th(j-c)}$	per diode				0.19	K/W
Module						
L_{CE}				18		nH
$R_{CC'+EE'}$	res., terminal-chip	$T_C = 25\text{ }^\circ\text{C}$		0.7		m Ω
		$T_C = 125\text{ }^\circ\text{C}$		1		m Ω
$R_{th(c-s)}$	per module			0.045		K/W
M_s	to heat sink (M5)		3		5	Nm
M_t		to terminals (M6)	2.5		5	Nm
						Nm
w					250	g
Temperature Sensor						
R_{100}	$T_C=100^\circ\text{C}$ ($R_{25}=5\text{ k}\Omega$)			$493 \pm 5\%$		Ω
$B_{100/125}$	$R_{(T)}=R_{100}\exp[B_{100/125}(1/T-1/T_{100})]$; $T[\text{K}]$;			$3550 \pm 2\%$		K



GB

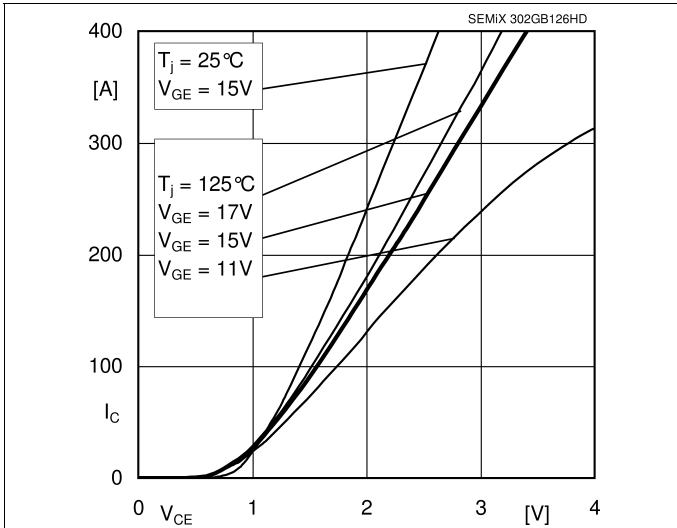


Fig. 1: Typ. output characteristic, inclusive $R_{CC'+ EE'}$

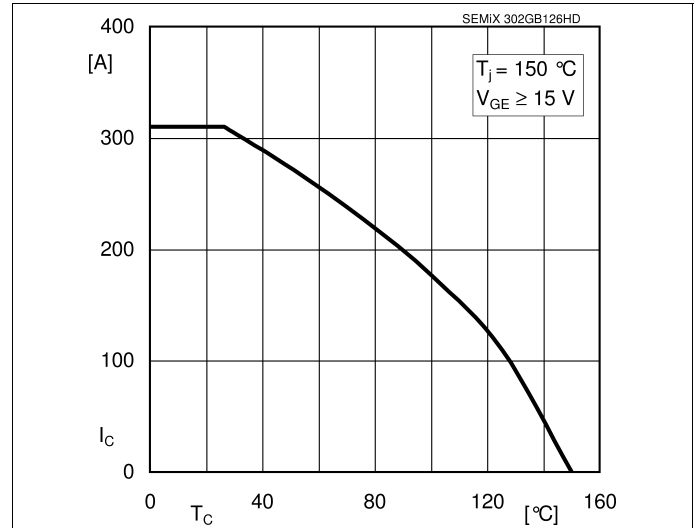


Fig. 2: Rated current vs. temperature $I_C = f(T_C)$

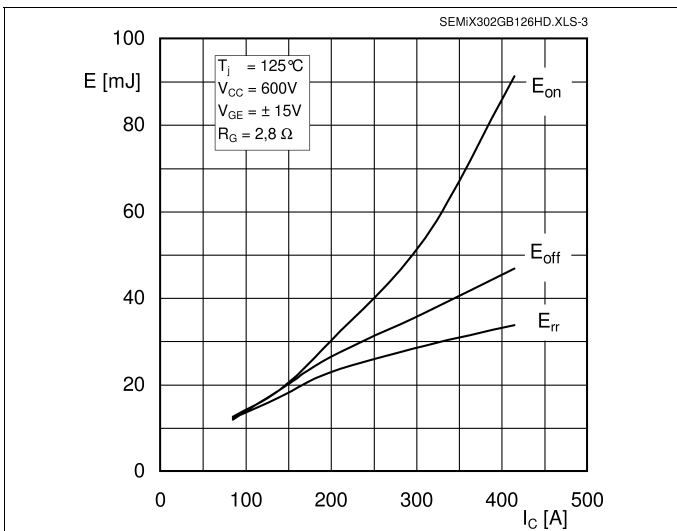


Fig. 3: Typ. turn-on /-off energy = $f(I_C)$

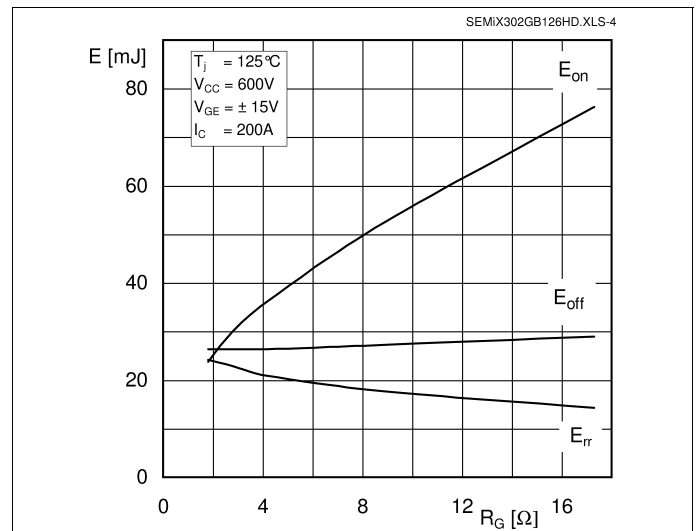


Fig. 4: Typ. turn-on /-off energy = $f(R_G)$

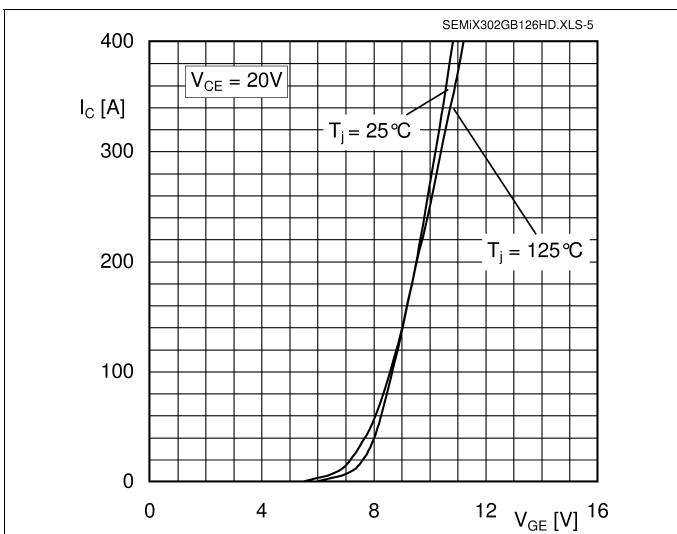


Fig. 5: Typ. transfer characteristic

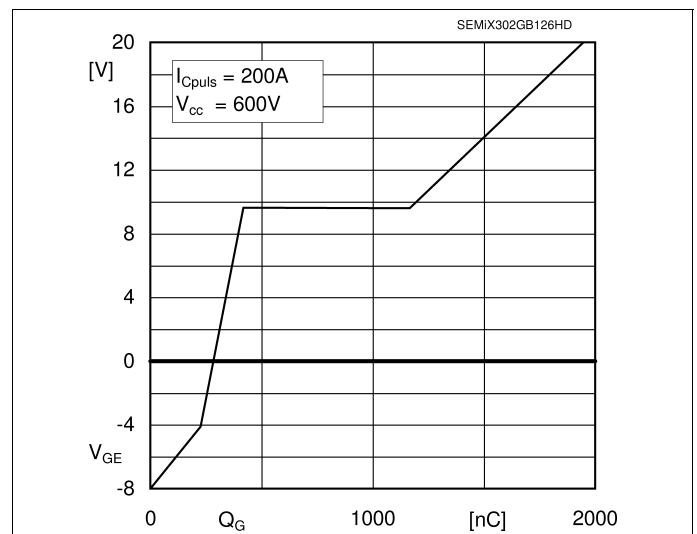


Fig. 6: Typ. gate charge characteristic

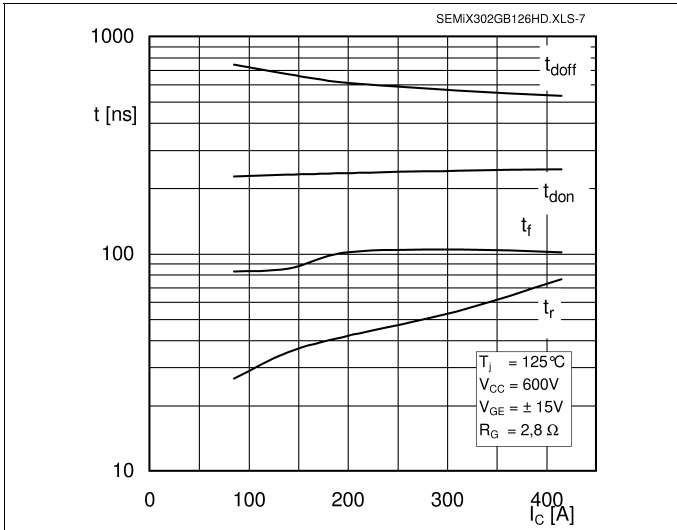


Fig. 7: Typ. switching times vs. I_C

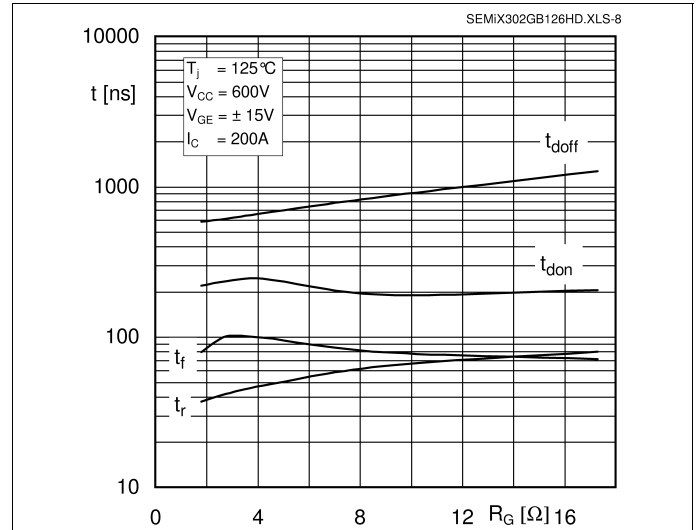


Fig. 8: Typ. switching times vs. gate resistor R_G

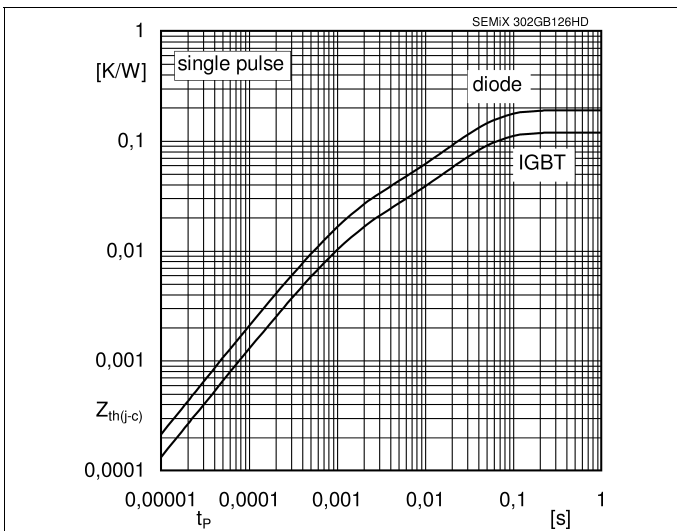


Fig. 9: Typ. transient thermal impedance

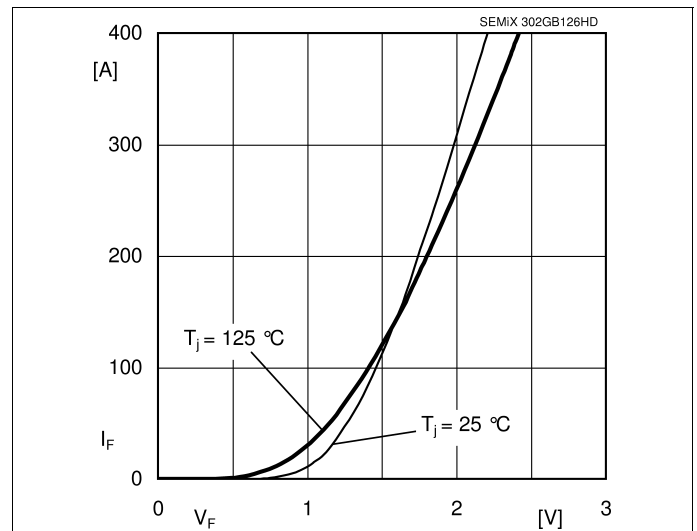


Fig. 10: Typ. CAL diode forward charact., incl. $R_{CC'+EE'}$

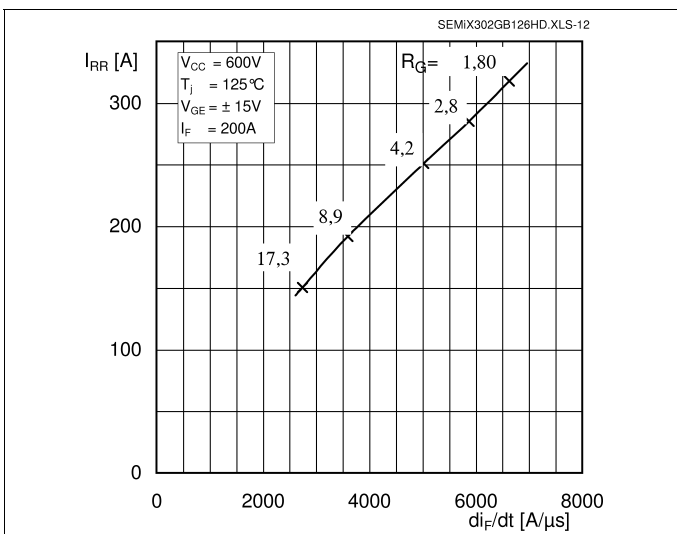


Fig. 11: Typ. CAL diode peak reverse recovery current

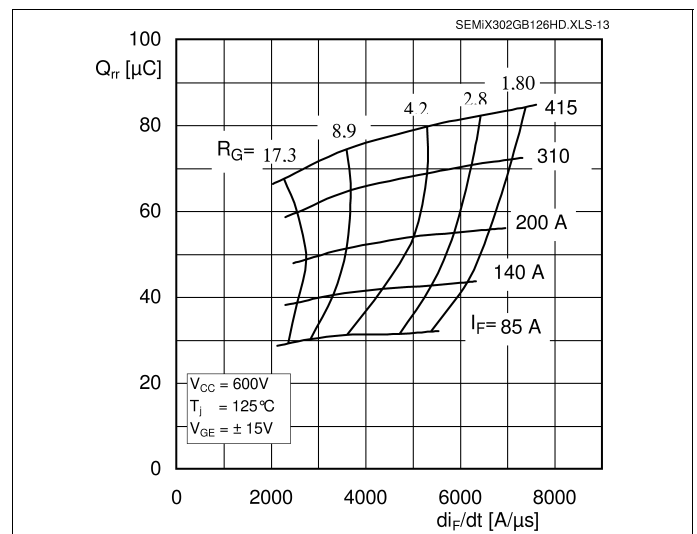
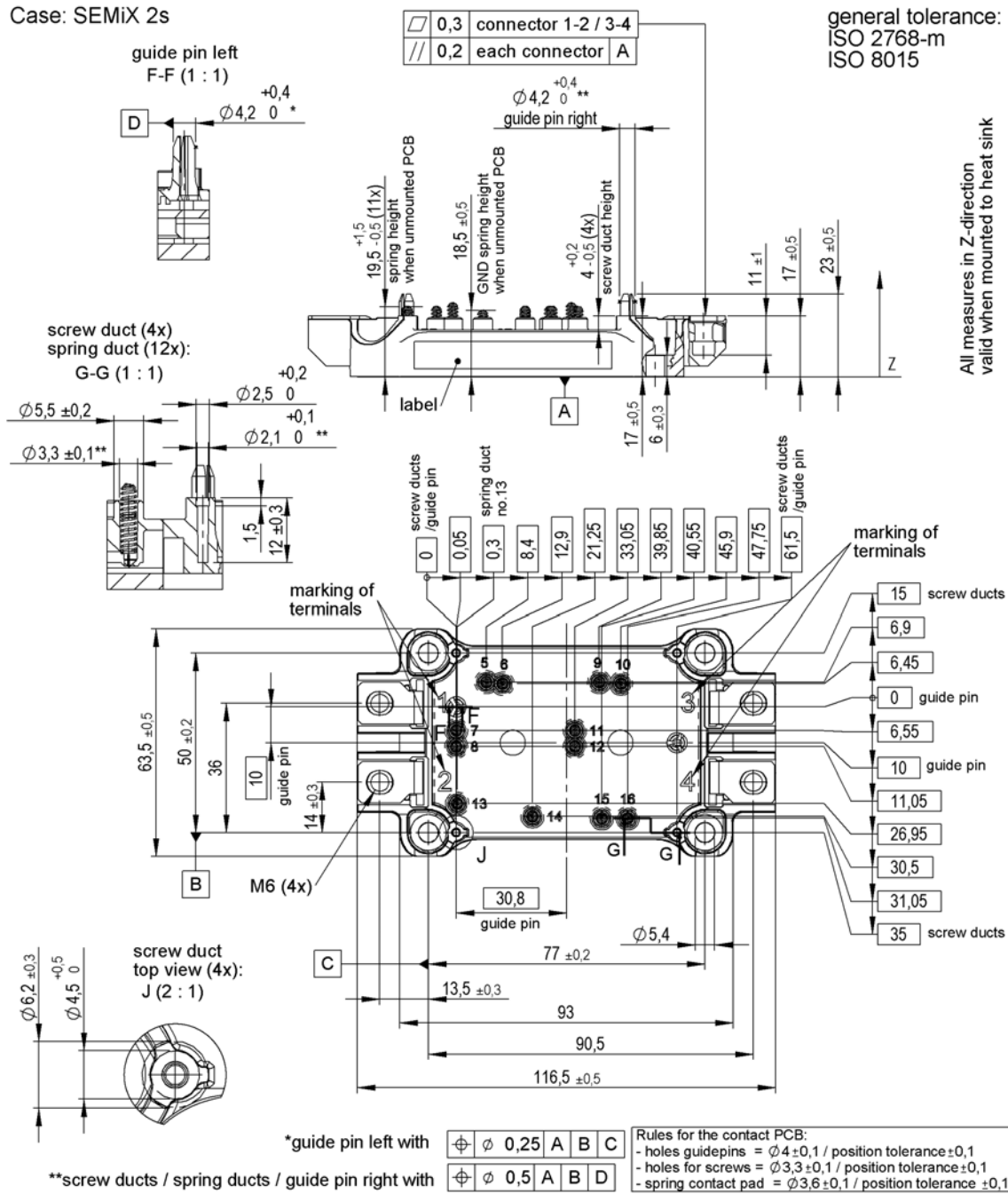


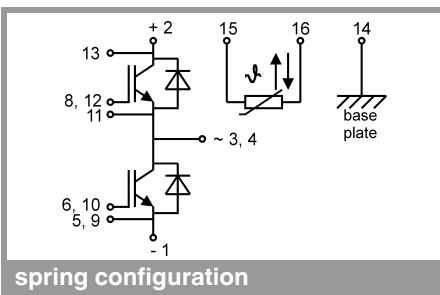
Fig. 12: Typ. CAL diode recovery charge

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Case: SEMiX 2s



SEMIX 2s



This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our staff.